

| L Number | Hits | Search Text | DB | Time stamp |
|----------|------|--|----------------------------|------------------|
| 3 | 22 | integrated with circuit with decoupling with capacitor.ti. | USPAT; US-PGPUB; JPO | 2004/07/15 08:06 |
| 4 | 0 | (integrated with circuit with decoupling with capacitor.ti.) and(float\$3 adj drain) | USPAT; US-PGPUB; JPO | 2004/07/15 08:07 |
| 5 | 2 | (integrated with circuit with decoupling with capacitor.ti.) and(drain) | USPAT; US-PGPUB; JPO | 2004/07/15 08:10 |
| 6 | 0 | decoupling with capacitor.ti. and(float\$3 adj drain) | USPAT; US-PGPUB; JPO | 2004/07/15 08:10 |
| 7 | 14 | decoupling with capacitor.ti. and(drain) | USPAT; US-PGPUB; JPO | 2004/07/15 08:11 |
| 8 | 6 | (decoupling with capacitor.ti. and(drain)) and(electrode) | USPAT; US-PGPUB; JPO | 2004/07/15 08:11 |
| 9 | 6 | ((decoupling with capacitor.ti. and(drain)) and(electrode)) and(source) | USPAT; US-PGPUB; JPO | 2004/07/15 08:15 |
| 10 | 131 | mos with capacitor.ti. | USPAT; US-PGPUB; JPO | 2004/07/15 08:15 |
| 11 | 2027 | semiconductor with capacitor.ti. | USPAT; US-PGPUB; JPO | 2004/07/15 08:15 |
| 12 | 86 | (mos with capacitor.ti.) and(electrode) | USPAT; US-PGPUB; JPO | 2004/07/15 08:16 |
| 13 | 49 | ((mos with capacitor.ti.) and(electrode)) and(drain and source) | USPAT; US-PGPUB; JPO | 2004/07/15 09:09 |
| 14 | 383 | (semiconductor with capacitor.ti.) and(drain adj region) | USPAT; US-PGPUB; JPO | 2004/07/15 08:21 |
| 15 | 218 | ((semiconductor with capacitor.ti.) and(drain adj region)) and(source adj region) | USPAT; US-PGPUB; JPO | 2004/07/15 08:21 |
| 16 | 211 | ((semiconductor with capacitor.ti.) and(drain adj region)) and(source adj region) and(electrode) | USPAT; US-PGPUB; JPO | 2004/07/15 08:21 |
| 17 | 188 | ((semiconductor with capacitor.ti.) and(drain adj region)) and(source adj region) and(electrode) and(dielectric) | USPAT; US-PGPUB; JPO | 2004/07/15 08:22 |
| 18 | 0 | ((semiconductor with capacitor.ti.) and(drain adj region)) and(source adj region) and(electrode) and(dielectric) and(BJT) | USPAT; US-PGPUB; JPO | 2004/07/15 08:22 |
| 19 | 174 | ((semiconductor with capacitor.ti.) and(drain adj region)) and(source adj region) and(electrode) and(dielectric) and(transistor) | USPAT; US-PGPUB; JPO | 2004/07/15 08:22 |
| 20 | 2 | "5371396" and(capacitor) | USPAT; US-PGPUB; JPO | 2004/07/15 09:17 |
| 21 | 14 | "6034388" | USPAT; US-PGPUB; JPO | 2004/07/15 09:33 |
| 22 | 278 | plurality with decoupling with capacitor | USPAT; US-PGPUB; JPO | 2004/07/15 10:08 |
| 23 | 15 | plurality near decoupling near capacitor | USPAT; US-PGPUB; JPO | 2004/07/15 09:34 |
| 24 | 0 | multi-fingered with decoupling adj capacitor | USPAT; US-PGPUB; JPO | 2004/07/15 09:35 |
| 25 | 0 | fingered with decoupling adj capacitor | USPAT; US-PGPUB; JPO | 2004/07/15 09:35 |

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| 26 | 0 | decoupling adj capacitor.ti. and(BJT) | USPAT; US-PGPUB; JPO | 2004/07/15 09:36 |
| 27 | 0 | decoupling adj capacitor.ti. and(parasitic near function) | USPAT; US-PGPUB; JPO | 2004/07/15 09:36 |
| 28 | 3 | decoupling adj capacitor.ti. and(bipolar near transistor) | USPAT; US-PGPUB; JPO | 2004/07/15 10:08 |
| 29 | 19 | plurality with capacitor.ti. | USPAT; US-PGPUB; JPO | 2004/07/15 10:10 |
| 30 | 144 | 361/306.2 and(plurality with capacitor) | USPAT; US-PGPUB; JPO | 2004/07/15 10:17 |
| 31 | 235 | integrated with circuit.ti. and(decoupling adj capacitor) | USPAT; US-PGPUB; JPO | 2004/07/15 10:17 |
| 32 | 152 | (integrated with circuit.ti. and(decoupling adj capacitor)) and(source) | USPAT; US-PGPUB; JPO | 2004/07/15 10:18 |
| 33 | 78 | ((integrated with circuit.ti. and(decoupling adj capacitor)) and(source)) and(drain) | USPAT; US-PGPUB; JPO | 2004/07/15 10:18 |
| 34 | 35 | ((integrated with circuit.ti. and(decoupling adj capacitor)) and(source)) and(drain)) and(electrode) | USPAT; US-PGPUB; JPO | 2004/07/15 10:18 |